# 2.5V Drive Nch+Nch MOS FET

# EM6K1

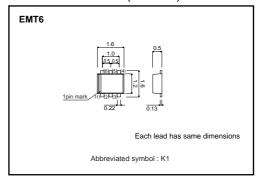
#### Structure

Silicon N-channel MOS FET

#### Features

- 1) Two 2SK3019 transistors in a single EMT package.
- 2) The MOS FET elements are independent, eliminating mutual interference.
- 3) Mounting cost and area can be cut in half.
- 4) Low on-resistance.
- 5) Low voltage drive (2.5V) makes this device ideal for portable equipment.

# ●External dimensions (Unit : mm)



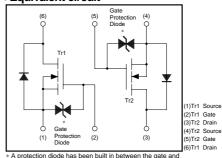
# Applications

Interfacing, switching (30V, 100mA)

## Packaging specifications

	Package	Taping
	Code	T2R
Туре	Basic ordering unit (pieces)	8000
EM6K1		0

# ●Equivalent circuit



A protection diode has been built in between the gate and
the source to protect against static electricity when the product
is in use. Use the protection circuit when rated voltages are exceeded

# ● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit	
Drain-source voltage		Voss	30	V	
Gate-source voltage		Vgss	±20	V	
Drain current	Continuous	lo	±100	mA	
	Pulsed	IDP *1	±400	mA	
Total power dissipation		Pp*2	150	mW / TOTAL	
		PD	120	mW / ELEMENT	
Channel temperature		Tch	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

<sup>\*2</sup> With each pin mounted on the recommended lands.

### ●Electrical characteristics (Ta=25°C)

<It is the same characteristics for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±1	μΑ	Vgs=±20V, Vps=0V
Drain-source breakdown voltage	V(BR)DSS	30	_	_	V	In=10μA, Vgs=0V
Zero gate voltage drain current	IDSS	_	_	1.0	μΑ	VDS=30V, VGS=0V
Gate threshold voltage	VGS(th)	0.8	_	1.5	V	Vps=3V, Ip=100μA
Static drain–source on–starte resistance	RDS(on)	_	5	8	Ω	In=10mA, Vgs=4V
	RDS(on)	_	7	13	Ω	In=1mA, Vgs=2.5V
Forward transfer admittance	Yfs	20	_	_	mS	Vps=3V, Ip=10mA
Input capacitance	Ciss	_	13	-	pF	V <sub>DS</sub> =5V
Output capacitance	Coss	_	9	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	4	_	pF	f=1MHz
Turn-on delay time	td(on)	_	15	-	ns	ID=10mA, VDD≒5V
Rise time	tr	_	35	-	ns	Vgs=5V
Turn-off delay time	td(off)	_	80	-	ns	RL=500Ω
Fall time	tf	_	80	_	ns	R <sub>G</sub> =10Ω

#### •Electrical characteristic curves

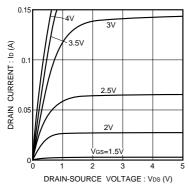


Fig.1 Typical Output Characteristics

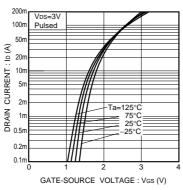


Fig.2 Typical Transfer Characteristics

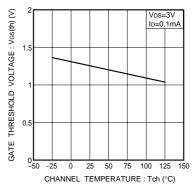


Fig.3 Gate Threshold Voltage vs. Channel Temperature

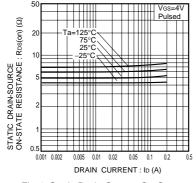


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

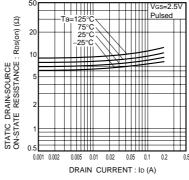


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

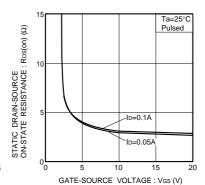


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

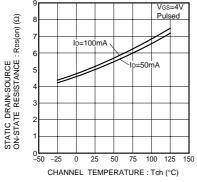


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

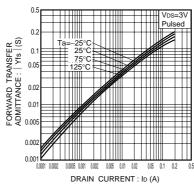


Fig.8 Forward Transfer Admittance vs. Drain Current

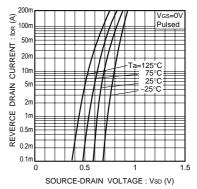


Fig.9 Reverse Drain Current vs. Source-Drain Voltage (I)

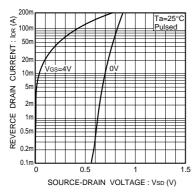


Fig.10 Reverse Drain Current vs. Source-Drain Voltage (II)

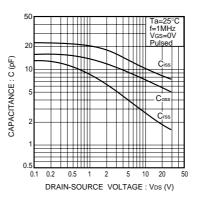


Fig.11 Typical Capacitance vs. Drain-Source Voltage

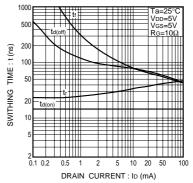


Fig.12 Switching Characteristics

#### Switching characteristics measurement circuits

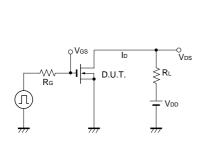


Fig.13 Switching Time Test Circuit

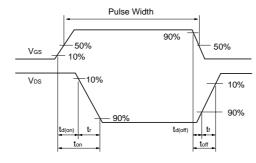


Fig.14 Switching Time Waveforms

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